

12GHz Low Noise FET in Dual Mold Plastic PKG

DESCRIPTION

- Low Noise and High Gain
- Original Dual Mold Plastic package

FEATURES

- Low noise figure and high associated gain
NF=0.42dB TYP., Ga=12.2dB TYP. @VDS=2V,
ID=10mA, f=12GHz

PACKAGE

- Flat-lead 4-pin thin-type super minimold package

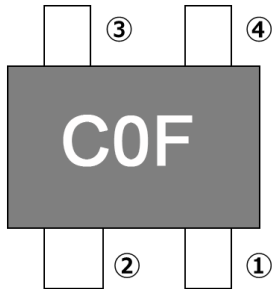


APPLICATIONS

- DBS LNB gain-stage, Mix-stage
- Low noise amplifier for microwave communication systems

ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Description
CE3514M4	CE3514M4-C2	Flat-lead 4-pin thin-type super minimold package	C0F	<ul style="list-style-type: none"> • Embossed tape 8 mm wide • Pin 1(Source), Pin 2 (Drain) Face the perforation side of the Tape • MOQ 15 kpcs/reel

PIN CONFIGURATION :


PIN No.	PIN Name
1	Source
2	Drain
3	Source
4	Gate

ABSOLUTE MAXIMUM RATINGS

(TA = +25°C, unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain to Source Voltage	V_{DS}	4.0	V
Gate to Source Voltage	V_{GS}	-3.0	V
Drain Current	I_D	I_{DSS}	mA
Gate Current	I_G	80	μA
Total Power Dissipation	P_{tot}	125	mW
Channel Temperature	T_{ch}	+150	°C
Storage Temperature	T_{stg}	-55 to +125	°C
Operation Temperature	T_{op}	-55 to +125 ^{Note}	°C

Note Refer to Total Power Dissipation vs. Ambient Temperature graph on page 4

RECOMMENDED OPERATING RANGE

(TA = +25°C, unless otherwise specified)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V_{DS}	+1	+2	+3	V
Drain Current	I_D	5	10	15	mA

ELECTRICAL CHARACTERISTICS

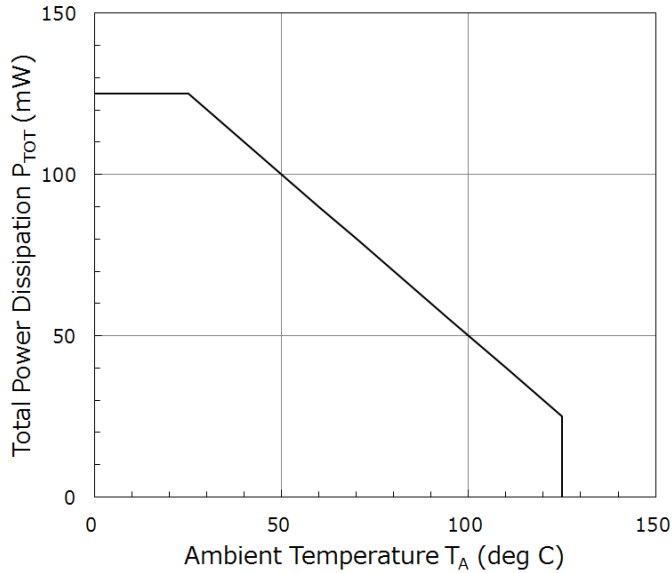
(TA = +25°C, unless otherwise specified)

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Gate to Source Leak Current	I_{GSO}	$V_{GS} = -3.0V$	-	0.4	10	μA
Saturated Drain Current	I_{DSS}	$V_{DS} = 2V, V_{GS} = 0V$	27	47.5	68	mA
Gate to Source Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = 2V, I_D = 120\mu A$	-1.10	-0.75	-0.39	V
Transconductance	Gm	$V_{DS} = 2V, I_D = 10mA$	54	69	-	mS
Noise Figure	NF	$V_{DS} = 2V, I_D = 10mA,$ $f = 12GHz$	-	0.42	0.62	dB
Associated Gain	Ga		10.5	12.2	-	dB

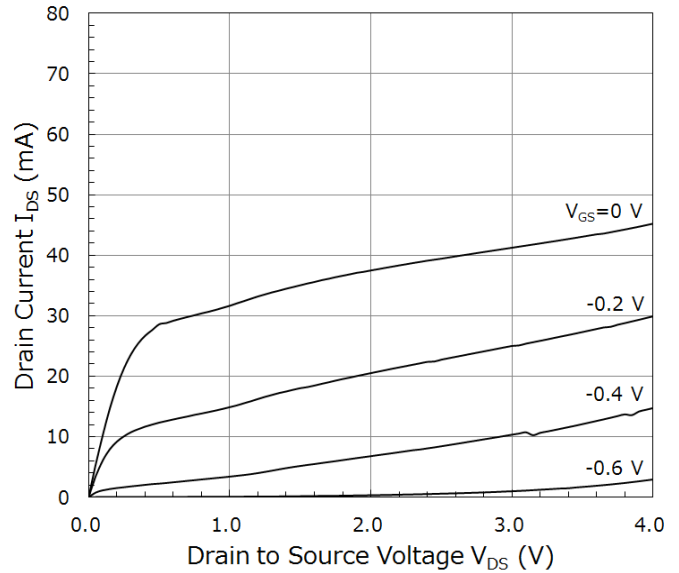
TYPICAL CHARACTERISTICS :

($T_A=+25^{\circ}\text{C}$, unless otherwise specified)

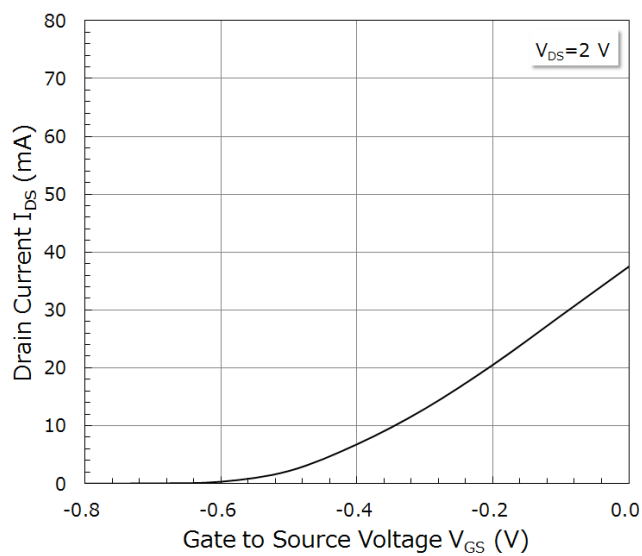
TOTAL POWER DISSIPATION VS. AMBIENT TEMPERATURE



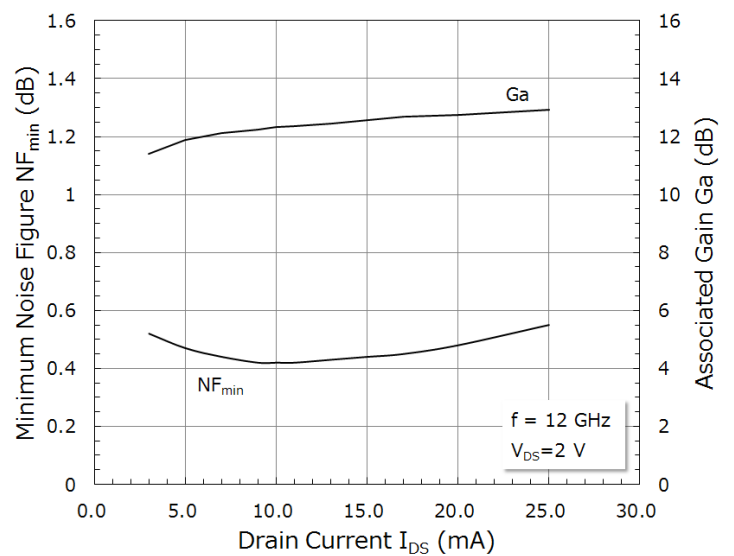
DRAIN CURRENT VS. DRAIN TO SOURCE VOLTAGE



DRAIN CURRENT VS. GATE TO SOURCE VOLTAGE



MINIMUM NOISE FIGURE & ASSOCIATED GAIN VS. DRAIN CURRENT



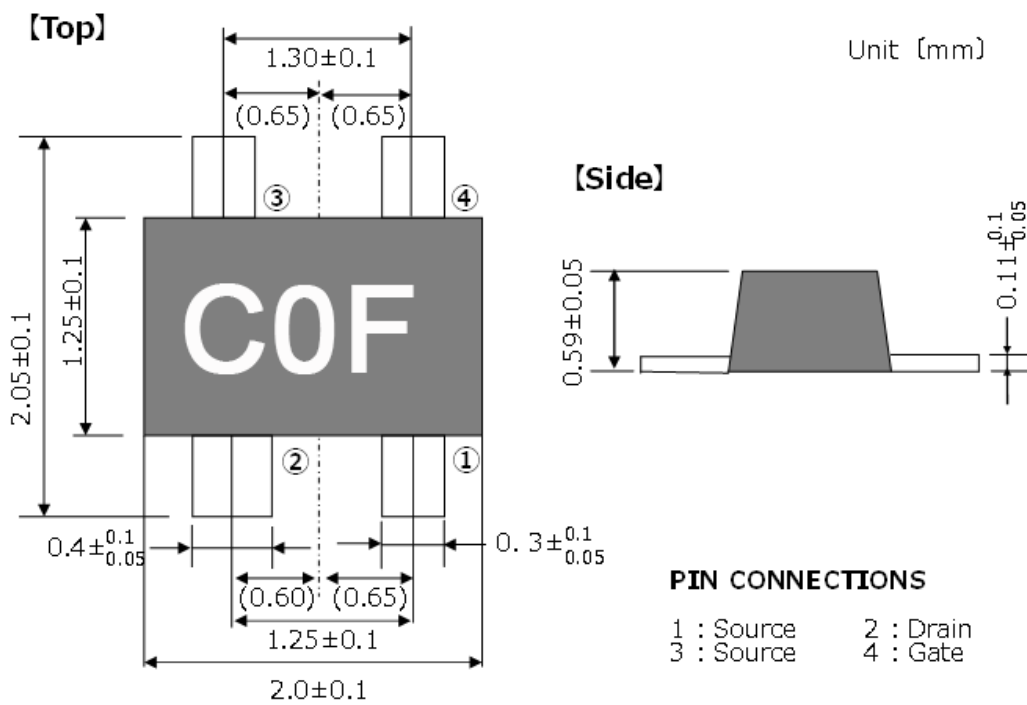
S-PARAMETERS

S-Parameters are available on the CEL web site.

RECOMMENDED SOLDERING CONDITIONS

Recommended Soldering Conditions are provided on the CEL web site.

PACKAGE DIMENSIONS



REVISION HISTORY

Version	Change to current version	Page(s)
CDS-0021-02 (Issue A) July 28, 2016	Initial datasheet	N/A

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